

To our customers,

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## Old Company Name in Catalogs and Other Documents

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Renesas Electronics website: <http://www.renesas.com>

April 1<sup>st</sup>, 2010  
Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (<http://www.renesas.com>)

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# HAT2140H

## Silicon N Channel Power MOS FET Power Switching

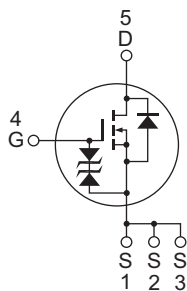
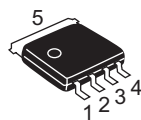
REJ03G1192-0400  
(Previous: ADE-208-1581B)  
Rev.4.00  
Sep 07, 2005

### Features

- Capable of 7 V gate drive
- Low drive current
- High density mounting
- Low on-resistance  
 $R_{DS(on)} = 12.5 \text{ m}\Omega$  typ. (at  $V_{GS} = 10 \text{ V}$ )

### Outline

RENESAS Package code: PTZZ0005DA-A  
(Package name: LFAK)



1, 2, 3 Source  
4 Gate  
5 Drain

## Absolute Maximum Ratings

(Ta = 25°C)

| Item                                   | Symbol                           | Value       | Unit |
|----------------------------------------|----------------------------------|-------------|------|
| Drain to source voltage                | $V_{DSS}$                        | 100         | V    |
| Gate to source voltage                 | $V_{GSS}$                        | ±20         | V    |
| Drain current                          | $I_D$                            | 25          | A    |
| Drain peak current                     | $I_{D(pulse)}$ <sup>Note 1</sup> | 100         | A    |
| Body-drain diode reverse drain current | $I_{DR}$                         | 25          | A    |
| Avalanche current                      | $I_{AP}$ <sup>Note 3</sup>       | 25          | A    |
| Avalanche energy                       | $E_{AR}$ <sup>Note 3</sup>       | 62.5        | mJ   |
| Channel dissipation                    | $P_{ch}$ <sup>Note 2</sup>       | 30          | W    |
| Channel temperature                    | $T_{ch}$                         | 150         | °C   |
| Storage temperature                    | $T_{stg}$                        | -55 to +150 | °C   |

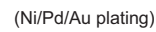
Notes: 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1\%$ 2.  $T_c = 25^\circ C$ 3. Value at  $T_{ch} = 25^\circ C$ ,  $R_g \geq 50 \Omega$ 

## Electrical Characteristics

(Ta = 25°C)

| Item                                       | Symbol        | Min | Typ  | Max  | Unit | Test Conditions                                                        |
|--------------------------------------------|---------------|-----|------|------|------|------------------------------------------------------------------------|
| Drain to source breakdown voltage          | $V_{(BR)DSS}$ | 100 | —    | —    | V    | $I_D = 10 \text{ mA}$ , $V_{GS} = 0$                                   |
| Gate to source breakdown voltage           | $V_{(BR)GSS}$ | ±20 | —    | —    | V    | $I_G = \pm 100 \mu A$ , $V_{DS} = 0$                                   |
| Gate to source leak current                | $I_{GSS}$     | —   | —    | ±10  | μA   | $V_{GS} = \pm 16 \text{ V}$ , $V_{DS} = 0$                             |
| Zero gate voltage drain current            | $I_{DSS}$     | —   | —    | 1    | μA   | $V_{DS} = 100 \text{ V}$ , $V_{GS} = 0$                                |
| Gate to source cutoff voltage              | $V_{GS(off)}$ | 2.0 | —    | 3.5  | V    | $V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ mA}$                         |
| Static drain to source on state resistance | $R_{DS(on)}$  | —   | 12.5 | 16.0 | mΩ   | $I_D = 12.5 \text{ A}$ , $V_{GS} = 10 \text{ V}$ <sup>Note 4</sup>     |
|                                            | $R_{DS(on)}$  | —   | 13.5 | 18.0 | mΩ   | $I_D = 12.5 \text{ A}$ , $V_{GS} = 7 \text{ V}$ <sup>Note 4</sup>      |
| Forward transfer admittance                | $ y_{fs} $    | 27  | 45   | —    | S    | $I_D = 12.5 \text{ A}$ , $V_{DS} = 10 \text{ V}$ <sup>Note 4</sup>     |
| Input capacitance                          | $C_{iss}$     | —   | 6500 | —    | pF   | $V_{DS} = 10 \text{ V}$                                                |
| Output capacitance                         | $C_{oss}$     | —   | 480  | —    | pF   | $V_{GS} = 0$                                                           |
| Reverse transfer capacitance               | $C_{rss}$     | —   | 210  | —    | pF   | $f = 1 \text{ MHz}$                                                    |
| Total gate charge                          | $Q_g$         | —   | 105  | —    | nC   | $V_{DD} = 50 \text{ V}$                                                |
| Gate to source charge                      | $Q_{gs}$      | —   | 20   | —    | nC   | $V_{GS} = 10 \text{ V}$                                                |
| Gate to drain charge                       | $Q_{gd}$      | —   | 22   | —    | nC   | $I_D = 25 \text{ A}$                                                   |
| Turn-on delay time                         | $t_{d(on)}$   | —   | 25   | —    | ns   | $V_{GS} = 10 \text{ V}$ , $I_D = 12.5 \text{ A}$                       |
| Rise time                                  | $t_r$         | —   | 24   | —    | ns   | $V_{DD} \approx 30 \text{ V}$                                          |
| Turn-off delay time                        | $t_{d(off)}$  | —   | 100  | —    | ns   | $R_L = 2.4 \Omega$                                                     |
| Fall time                                  | $t_f$         | —   | 12   | —    | ns   | $R_g = 4.7 \Omega$                                                     |
| Body-drain diode forward voltage           | $V_{DF}$      | —   | 0.83 | 1.08 | V    | $I_F = 25 \text{ A}$ , $V_{GS} = 0$ <sup>Note 4</sup>                  |
| Body-drain diode reverse recovery time     | $t_{rr}$      | —   | 55   | —    | ns   | $I_F = 25 \text{ A}$ , $V_{GS} = 0$<br>$di_F/dt = 100 \text{ A}/\mu s$ |

Note: 4. Pulse test

Unit: mm

| Part Name     | Quantity | Shipping Container |
|---------------|----------|--------------------|
| HAT2140H-EL-E | 2500 pcs | Taping             |

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